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|---|--|
| Title of Change: | Fabrication Site Transfer from BE2 (Belgium 6") to Fab10 (Pocatello, Id 8") |
| Proposed Changed Material First Ship Date: | 13 Dec 2022 or earlier if approved by customer |
| Current Material Last Order Date: | 01 Sep 2021 <i>Orders received after the Current Material Last Order Date expiration are to be considered as orders for new changed material as described in this PCN. Orders for current (unchanged) material after this date will be per mutual agreement and current material inventory availability.</i> |
| Current Material Last Delivery Date: | 12 Dec 2022 <i>The Current Material Last Delivery Date may be subject to change based on build and depletion of the current (unchanged) material inventory</i> |
| Product Category: | Active components – Discrete components |
| Contact information: | Contact your local ON Semiconductor Sales Office or NoorArdila.Shaharuddin@onsemi.com |
| PCN Samples Contact: | Contact your local ON Semiconductor Sales Office to place sample order or <PCN.samples@onsemi.com> . Sample requests are to be submitted no later than 45 days after publication of this change notification. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements. |
| Additional Reliability Data: | Contact your local ON Semiconductor Sales Office or Nicky.Siu@onsemi.com |
| Type of Notification: | This is an Initial Product/Process Change Notification (IPCN) sent to customers. An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 12 months prior to implementation of the change. In case of questions, contact <PCN.Support@onsemi.com> . |

Change Category

| Category | Type of Change |
|----------------------------|---|
| Process - Wafer Production | Move of all or part of wafer fab to a different location/site/subcontractor Change of gate material / dielectrics, New wafer diameter |

Description and Purpose:

| | Before Change Description | After Change Description |
|----------------------|---------------------------------|---|
| <i>Bond Wire</i> | Au wire | Au wire Cu wire (<i>part numbers with ** in Qualification Vehicle list only</i>) |
| <i>Other Changes</i> | Wafer manufacturing in Fab2 BE2 | Wafer manufacturing in Fab10 USU |

There is no product marking change as a result of this change.



| | |
|---|---|
| Reason / Motivation for Change: | Acquisition |
| Anticipated impact on fit, form, function, reliability, product safety or manufacturability: | The device has been qualified and validated based on the same Product Specification. The device has successfully passed the qualification tests. Potential impacts can be identified, but due to testing performed by ON Semiconductor in relation to the PCN, associated risks are verified and excluded. No anticipated impacts. |

Sites Affected:

| ON Semiconductor Sites | External Foundry/Subcon Sites |
|---|-------------------------------|
| ON Semiconductor Oudenaarde, Belgium | None |
| ON Semiconductor Pocatello Idaho, United States | |

Marking of Parts/ Traceability of Change:

Affected parts with this changing will be identified by the date code

Reliability Data Summary:

QV1 DEVICE NAME: SESD7L5.0DT5G

RMS: TBC

PACKAGE: SOT-723-3

| Test | Specification | Condition | Interval |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

QV2 DEVICE NAME: SESD9L5.0ST5G

RMS: TBC

PACKAGE: SOD923

| Test | Specification | Condition | Interval |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

**QV4 DEVICE NAME: SZCM1213A-04SO****RMS: TBC****PACKAGE: SC-74**

| Test | Specification | Condition | Interval |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

QV5 DEVICE NAME: SZESD7008MUTAG**RMS: TBC****PACKAGE: 5.5x1.5 UDFN-18**

| Test | Specification | Condition | Interval |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

QV6 DEVICE NAME: SZNUP4114HMR6T1G**RMS: TBC****PACKAGE: TSOP-6**

| Test | Specification | Condition | Interval |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

QV7 DEVICE NAME: ESDR0502NMUTAG**RMS: TBC****PACKAGE: UDFN-6 1.2x1**

| Test | Specification | Condition | Interval |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 1008 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 96 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

QV10 DEVICE NAME: SZESD7104MTWTAGRMS: TBCPACKAGE: 2.5x1.0 WDFNW-10

| Test | Specification | Condition | Interval |
|------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |

Electrical Characteristics Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the [PCN Customized Portal](#).

| Current Part Number | New Part Number | Qualification Vehicle |
|---------------------|-----------------|---|
| SESD7L5.0DT5G | N/A | QV#1 |
| SESD9L5.0ST5G | N/A | QV#2 |
| SZESD7951ST5G | N/A | QBS to SESD9L5.0ST5G (QV#2) |
| SZESD9L3.3ST5G | N/A | QBS to SESD9L5.0ST5G (QV#2) |
| SZESD9R3.3ST5G | N/A | QBS to SESD9L5.0ST5G (QV#2) |
| SZESD7004MUTAG | N/A | QBS to SZESD7008MUTAG (QV#5) ** |
| SZESD7008MUTAG | N/A | QV#5 ** |
| SZESD7016MUTAG | N/A | QBS to SZESD7008MUTAG (QV#5) ** |
| SZESD7104MUTAG | N/A | QBS to SZESD7008MUTAG (QV#5), ESDR0502NMUTAG (QV#7) ** |
| SZESD7104MTWTAG | N/A | QV#10 ** |
| SZESD9M5.0ST5G | N/A | QBS to SESD9L5.0ST5G (QV#2) |
| SZCM1213A-04SO | N/A | QV#4 |
| SZNUP4114UCLW1T2G | N/A | QBS to SZCM1213A-04SO (QV#4) |
| SZNUP4114HMR6T1G | N/A | QV#6 ** |
| SNUP2114UCMR6T1G | N/A | QBS to SZNUP4114HMR6T1G (QV#6) ** |
| SZESDR0502BT1G | N/A | QBS to SESD7L5.0DT5G (QV#1), SZCM1213A-04SO (QV#4) |
| SZMG2040MUTAG | N/A | QBS to SZESD7008MUTAG (QV#5) ** |

Japanese translation of the notification starts here.
通知の日本語訳はここから始まります。

Note: The Japanese version is for reference only. In case of any differences between the English and Japanese version, the English version shall control.

注：日本語版は参照用です。英語版と日本語版の違いがある場合は、英語版が優先されます。



初回製品 / プロセス変更通知

文書番号 : IPCN23751Z

発行日 : 03 Mar 2021

| | | |
|---------------------------|--|---|
| 変更件名: | BE2 (ベルギー 6 インチ) から Fab10 (アイダホ州ボカテロ 8 インチ) へのウェハー製造拠点移管 | |
| 初回出荷予定日: | 13 Dec 2022 またはお客様からの承認が得られた場合はそれ以前。 | |
| 現在の材料の最終注文日: | 01 Sep 2021 既存品の最終注文日以降の注文は、この PCN に記載されている変更後品の注文とみなされます。この日付より後の既存品(変更前品)の注文は、相互契約により変更前品の在庫状況に応じて履行されます。 | |
| 現在の材料の最終出荷日: | 12 Dec 2022 既存品(変更前品)の最終出荷日は、変更前品の製造および在庫の状況によって変更されることがあります。 | |
| 製品カテゴリ: | アクティブなコンポーネント - 個別コンポーネント | |
| 連絡先情報: | 現地のオン・セミコンダクター営業所または < NoorArdila.Shaharuddin@onsemi.com > にお問い合わせください。 | |
| サンプル: | 現地のオン・セミコンダクター営業所に注文するか、または< PCN.samples@onsemi.com >にお問い合わせください。サンプルは、この変更通知の発行から 45 日以内に要求してください。サンプル納入時は、依頼日、数量、特別梱包材/ラベル条件によって異なります。 | |
| 追加の信頼性データ: | お客さまの地域のオン・セミコンダクター営業所または Nicky.Siu@onsemi.com > にお問い合わせください。 | |
| 通知種別: | これは、お客様宛の初回製品 / プロセス変更通知 (IPCN) です。IPCN は、近日中に実施される変更に関する事前通知であり、変更の詳細および影響を受けるデバイスについての一般情報が記載されます。また、暫定的な信頼性認証計画も記載されます。 最終的な認定データおよび特性データは最終製品 / プロセス変更通知 (FPCN) に含まれます。この IPCN は、変更実施から少なくとも 12 か月前に発行される最終製品 / プロセス変更通知 (FPCN) に先だって通知されます。ご不明な点がございましたら、< PCN.Support@onsemi.com > にお問い合わせください。 | |
| 変更カテゴリ: | 変更種別 | |
| プロセス-ウェハー製造 | ウェハー工場のすべてまたは一部の異なる場所/拠点/外注先への移管 ゲート材料/絶縁体の変更 新しいウェハー径 | |
| 説明および目的: | | |
| | 変更前の表記 | 変更後の表記 |
| ボンドワイヤ | Au ワイヤ | Au ワイヤ Cu ワイヤ (認定試験用ビークルの一覧に** が付いている製品番号のみ) |
| その他の変更 | Fab2 BE2 でウェハー製造 | Fab10 USU でウェハー製造 |
| 今回の変更に伴う製品マーキングの変更はありません。 | | |



| | |
|---|---|
| 変更の理由 / 動機: | 買収 |
| 適合性、形状、機能、信頼性、製品安全性、または製造可能性に関して見込まれる影響 | 製品は同じ製品仕様に基づいて認定および検証されています。製品は認定試験に正常に合格しています。潜在的な影響が確認される可能性があります。オン・セミコンダクターが PCN に関して実施する検査により、関連するリスクは検証および排除されます。 予想される影響はありません。 |
| 影響を受ける拠点: | |
| オン・セミコンダクター拠点: | 外部製造工場 / 下請業者拠点: |
| ON Semiconductor Oudenaarde, Belgium | なし |
| ON Semiconductor Pocatello Idaho, United States | |
| 部品の表示 / 変更の追跡可能性: | この変更により影響を受ける製品は、日付コードにより識別されます。 |

信頼性データの要約:

デバイス名 : SESD7L5.0DT5G

RMS: TBC

パッケージ: SOT-723-3

| テスト | 仕様 | 条件 | 間隔 |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

デバイス名 : SESD9L5.0ST5G

RMS: TBC

パッケージ: SOD923

| テスト | 仕様 | 条件 | 間隔 |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

デバイス名 : SZCM1213A-04SORMS: TBCパッケージ: SC-74

| テスト | 仕様 | 条件 | 間隔 |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

デバイス名 : SZESD7008MUTAGRMS: TBCパッケージ: 5.5x1.5 UDFN-18

| テスト | 仕様 | 条件 | 間隔 |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

デバイス名: SZNUP4114HMR6T1GRMS: TBCパッケージ: TSOP-6

| テスト | 仕様 | 条件 | 間隔 |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

デバイス名: ESDR0502NMUTAGRMS: TBCパッケージ: UDFN-6 1.2x1

| テスト | 仕様 | 条件 | 間隔 |
|-------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| HTSL | JESD22-A103 | Ta =Max rate storage temp for device = 150°C | 1008 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 96 hrs |
| uHAST | JESD22-A118 | Temp = 130°C, RH=85%, ~ 18.8 psig | 96 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |
| RSH | JESD22- B106 | Ta=265°C 10 sec dwell B106 | |

デバイス名: SZESD7104MTWTAGRMS: TBCパッケージ: 2.5x1.0 WDFNW-10

| テスト | 仕様 | 条件 | 間隔 |
|------|---------------------|--|----------|
| HTRB | JESD22-A108 | Tj = Max rate = 150°C for device, bias = 100% of rated V for Q 101 Rev D | 2016 hrs |
| TC | JESD22-A104 | Temp = -65°C to +150°C; for 1000 cycles | 1000 cyc |
| HAST | JESD22-A110 | Temp = 130°C, 85% RH, ~18.8 psig, bias = 80% of rated V or 100V max | 192 hrs |
| PC | J-STD-020 JESD-A113 | IR reflow at 245°C or 260°C (pkg dependant) | |

電気的特性の要約:

電気的特性への影響はありません。

影響を受ける部品の一覧:

注: 標準の部品番号(既製品)のみが部品一覧に記載されます。本 PCN に影響を受けるカスタム 部品は、PCN メールのお客様の特定の PCN の付属文書、または PCN カスタマイズポータルに記載されています。

| 現在の部品番号 | 新部品番号 | 認定試験用ピークル |
|-------------------|-------|---|
| SESD7L5.0DT5G | N/A | QV#1 |
| SESD9L5.0ST5G | N/A | QV#2 |
| SZESD7951ST5G | N/A | QBS to SESD9L5.0ST5G (QV#2) |
| SZESD9L3.3ST5G | N/A | QBS to SESD9L5.0ST5G (QV#2) |
| SZESD9R3.3ST5G | N/A | QBS to SESD9L5.0ST5G (QV#2) |
| SZESD7004MUTAG | N/A | QBS to SZESD7008MUTAG (QV#5) ** |
| SZESD7008MUTAG | N/A | QV#5 ** |
| SZESD7016MUTAG | N/A | QBS to SZESD7008MUTAG (QV#5) ** |
| SZESD7104MUTAG | N/A | QBS to SZESD7008MUTAG (QV#5), ESDR0502NMUTAG (QV#7) ** |
| SZESD7104MTWTAG | N/A | QV#10 ** |
| SZESD9M5.0ST5G | N/A | QBS to SESD9L5.0ST5G (QV#2) |
| SZCM1213A-04SO | N/A | QV#4 |
| SZNUP4114UCLW1T2G | N/A | QBS to SZCM1213A-04SO (QV#4) |
| SZNUP4114HMR6T1G | N/A | QV#6 ** |
| SNUP2114UCMR6T1G | N/A | QBS to SZNUP4114HMR6T1G (QV#6) ** |
| SZESDR0502BT1G | N/A | QBS to SESD7L5.0DT5G (QV#1), SZCM1213A-04SO (QV#4) |
| SZMG2040MUTAG | N/A | QBS to SZESD7008MUTAG (QV#5) ** |